

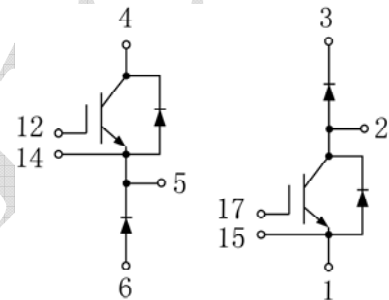
# GT75CH120T2H

## IGBT Module

### Preliminary Data

#### Features:

- Short Circuit Rated 10 $\mu$ s
- Low Saturation Voltage:  $V_{CE(sat)} = 1.90V @ I_C = 75A, T_C = 25^\circ C$
- Low Switching Loss
- 100% RBSOA Tested ( $2 \times I_C$ )
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



#### Applications:

- Industrial Motor Drive
- UPS, SMPS
- Servo Drive, Switched Reluctance Drive

#### IGBT, Brake-Chopper

#### Maximum Rated Values ( $T_C = 25^\circ C$ Unless otherwise specified)

$V_{CES}$	Collector-Emitter Blocking Voltage		1200	V
$V_{GES}$	Gate-Emitter Voltage		$\pm 20$	V
$I_C$	Continuous Collector Current	$T_C = 80^\circ C,$	75	A
		$T_C = 25^\circ C$	135	A
$I_{CM}$	Peak Collector Current Repetitive	$T_J = 175^\circ C$	150	A
$t_{SC}$	Short Circuit Withstand Time		>10	$\mu s$
$P_D$	Maximum Power Dissipation (IGBT)	$T_C = 25^\circ C$ $T_{Jmax} = 175^\circ C$	517	W

## Electrical Characteristics of IGBT ( $T_C=25^{\circ}\text{C}$ Unless otherwise specified)

### Static characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 1\text{mA}, V_{CE} = V_{GE}$	5.0	5.5	6.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 75\text{A}, V_{GE} = 15\text{V}$	$T_J = 25^{\circ}\text{C}$	1.90	2.20	V
			$T_J = 125^{\circ}\text{C}$	2.20		V
$I_{CES}$	Collector-Emitter Leakage Current	$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_J = 25^{\circ}\text{C}$			1	mA
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}, T_J = 25^{\circ}\text{C}$			200	nA
$C_{ies}$	Input Capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		10.4		nF
$C_{oes}$	Output capacitance			0.38		nF
$C_{res}$	Reveres transfer capacitance			0.26		nF

### Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 600\text{V}, I_C = 75\text{A}, R_G = 15\Omega, V_{GE} = \pm 15\text{V},$ Inductive Load	$T_J = 25^{\circ}\text{C}$		190		ns
			$T_J = 125^{\circ}\text{C}$		170		
$t_r$	Rise Time		$T_J = 25^{\circ}\text{C}$		100		ns
			$T_J = 125^{\circ}\text{C}$		110		
$t_{d(off)}$	Turn-off Delay Time		$T_J = 25^{\circ}\text{C}$		380		ns
			$T_J = 125^{\circ}\text{C}$		400		
$t_f$	Fall Time		$T_J = 25^{\circ}\text{C}$		150		ns
			$T_J = 125^{\circ}\text{C}$		200		
$E_{on}$	Turn-on Switching Loss		$T_J = 25^{\circ}\text{C}$		5.7		mJ
			$T_J = 125^{\circ}\text{C}$		6.9		
$E_{off}$	Turn-off Switching Loss	$T_J = 25^{\circ}\text{C}$		3.5		mJ	
		$T_J = 125^{\circ}\text{C}$		5.6			
$Q_g$	Total Gate Charge	$T_J = 25^{\circ}\text{C}$		630		nC	
RBSOA	RBSOA	$I_C=150\text{A}, V_{CC}=1050\text{V}, V_p=1200\text{V}, R_g = 15\Omega, V_{GE}=\pm 15\text{V to } 0\text{V}, T_J = 150^{\circ}\text{C}$	Trapezoid				
SCSOA	SCSOA	$V_{CC} = 600\text{V}, V_{GE} = 15\text{V}, T_J = 150^{\circ}\text{C}$	10			$\mu\text{s}$	
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case			0.29		$^{\circ}\text{C/W}$	

### Diode, Reverse

#### Maximum Rated Values ( $T_C=25^{\circ}\text{C}$ Unless otherwise specified)

$V_{RRM}$	Repetitive peak reverse voltage	1200	V
$I_F$	Diode Continuous Forward Current	75	A
$I_{FM}$	Peak FWD Current Repetitive	150	A

#### Electrical Characteristics of FWD ( $T_C=25^{\circ}\text{C}$ Unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{FM}$	Forward Voltage	$I_F = 75\text{A}$ , $V_{GE} = 0\text{V}$	$T_J = 25^{\circ}\text{C}$	2.00	2.20	V
			$T_J = 125^{\circ}\text{C}$	2.20		
$I_{rr}$	Peak Reverse Recovery Current		$T_J = 25^{\circ}\text{C}$	35		A
			$T_J = 125^{\circ}\text{C}$	40		
$Q_{rr}$	Reverse Recovery Charge	$I_F = 75\text{A}$ , $di/dt = 660\text{A}/\mu\text{s}$ , $V_{rr} = 600\text{V}$ , $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	3.5		$\mu\text{C}$
			$T_J = 125^{\circ}\text{C}$	9.5		
$E_{rec}$	Reverse Recovery Energy		$T_J = 25^{\circ}\text{C}$	1.1		mJ
			$T_J = 125^{\circ}\text{C}$	3.7		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case			0.56		$^{\circ}\text{C}/\text{W}$

### Diode, Brake-Chopper

#### Maximum Rated Values ( $T_C=25^{\circ}\text{C}$ Unless otherwise specified)

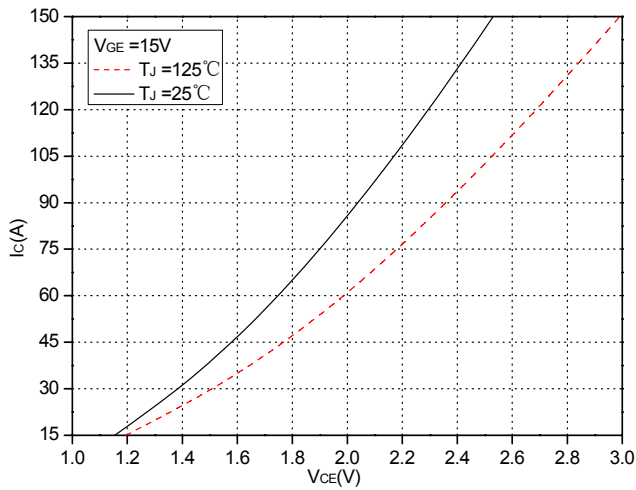
$V_{RRM}$	Repetitive peak reverse voltage	1200	V
$I_F$	Diode Continuous Forward Current	75	A
$I_{FM}$	Peak FWD Current Repetitive	150	A

### Electrical Characteristics of FWD ( $T_C=25^{\circ}\text{C}$ Unless otherwise specified)

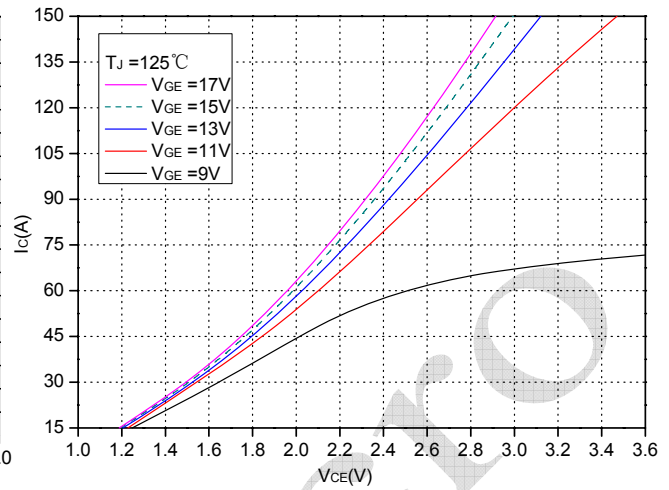
Symbol	Description	Conditions	Min	Typ	Max	Unit	
$V_{FM}$	Forward Voltage	$I_F = 75\text{A}$ , $V_{GE} = 0\text{V}$	$T_J = 25^{\circ}\text{C}$		1.80	2.00	V
			$T_J = 125^{\circ}\text{C}$		2.00		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case			0.41		$^{\circ}\text{C}/\text{W}$	

### Module

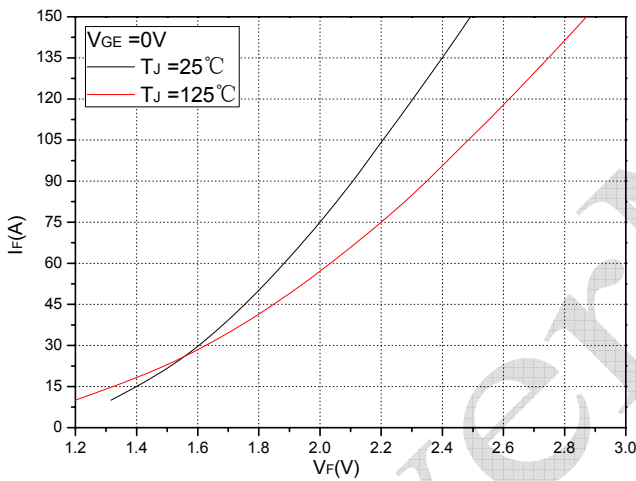
Symbol	Description	Min	Typ	Max	Unit	
$V_{iso}$	Isolation Voltage(All Terminals Shorted)	$f = 50\text{Hz}$ , 1minute	2500		V	
$T_J$	Maximum Junction Temperature			175	$^{\circ}\text{C}$	
$T_{JOP}$	Maximum Operating Junction Temperature Range		-40 +150		$^{\circ}\text{C}$	
$T_{stg}$	Storage Temperature		-40 +125		$^{\circ}\text{C}$	
$R_{\theta CS}$	Case-To-Sink (Conductive Grease Applied)			0.03	$^{\circ}\text{C}/\text{W}$	
M	Power Terminals Screw:M5		3.0		5.0	N·m
M	Mounting Screw:M6		4.0		6.0	N·m
G	Weight			280		g



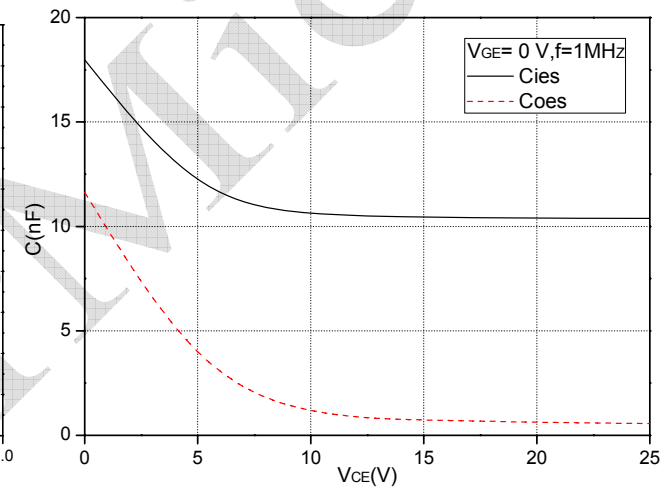
**Fig.1 Typical Saturation Voltage Characteristics**



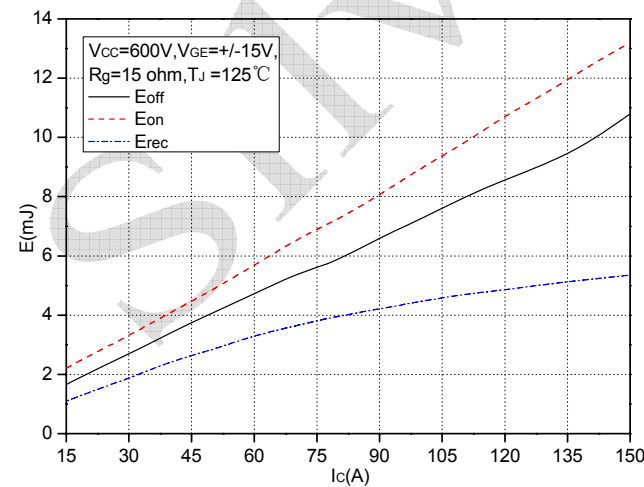
**Fig.2 Typical Output Characteristics**



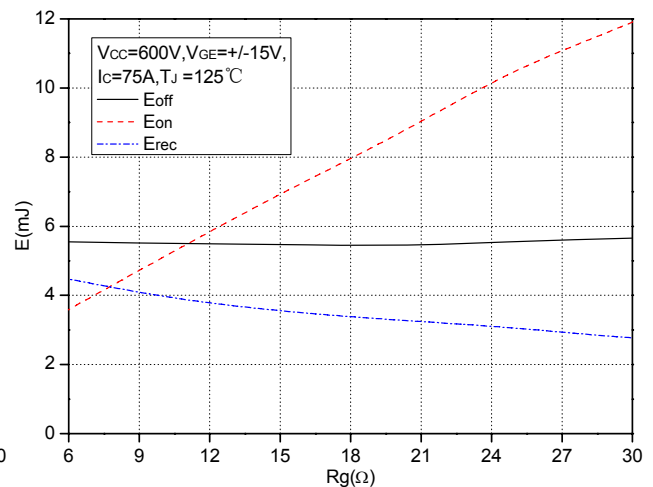
**Fig.3 Forward Characteristics of FWD (Reverse)**



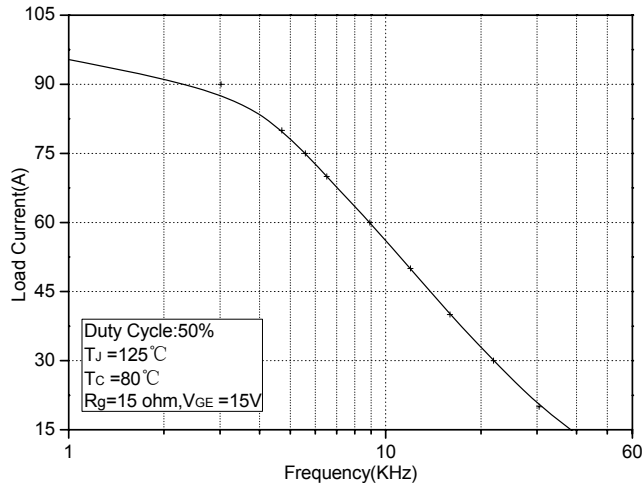
**Fig.4 Capacitance Characteristics**



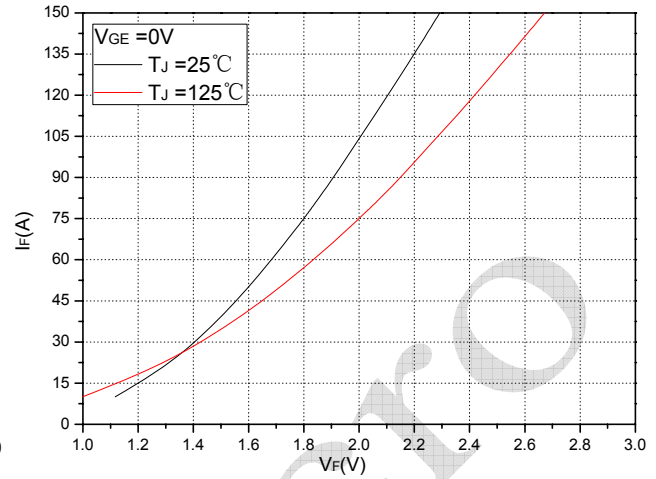
**Fig.5 Typical Switching Loss vs. Collector Current**



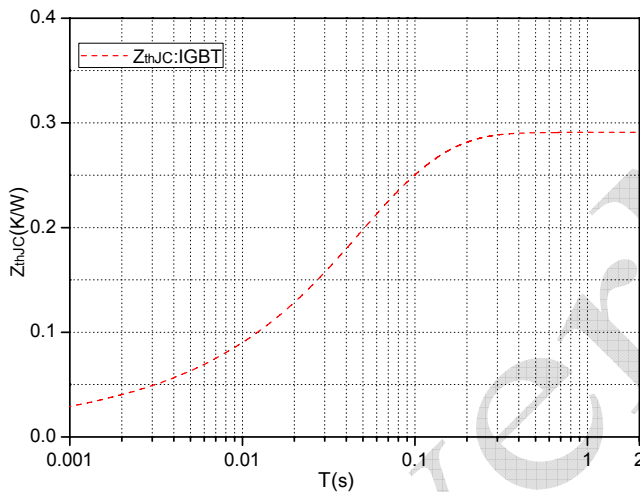
**Fig.6 Typical Switching Loss vs. Gate Resistance**



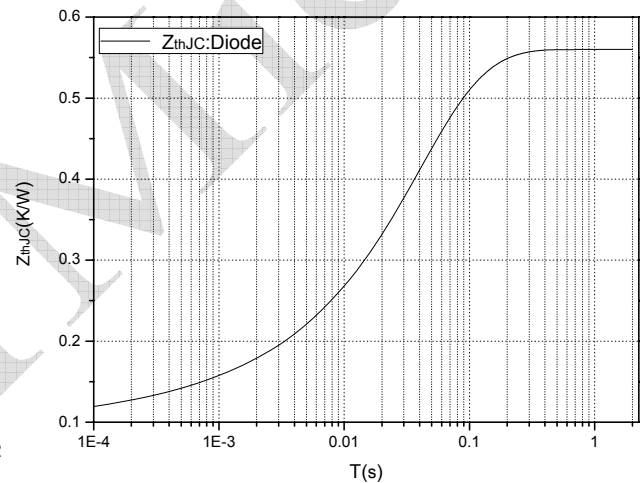
**Fig.7 Typical Load Current vs. Frequency**



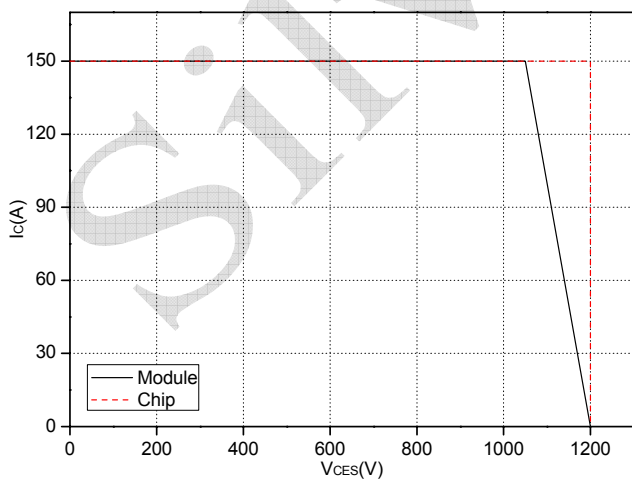
**Fig.8 Forward Characteristics of Diode (Brake-Chopper)**



**Fig.9 Transient thermal impedance (IGBT)**

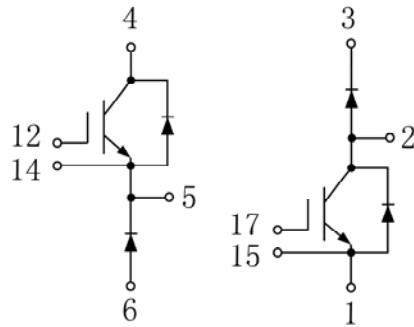


**Fig.10 Transient thermal impedance (Diode)**

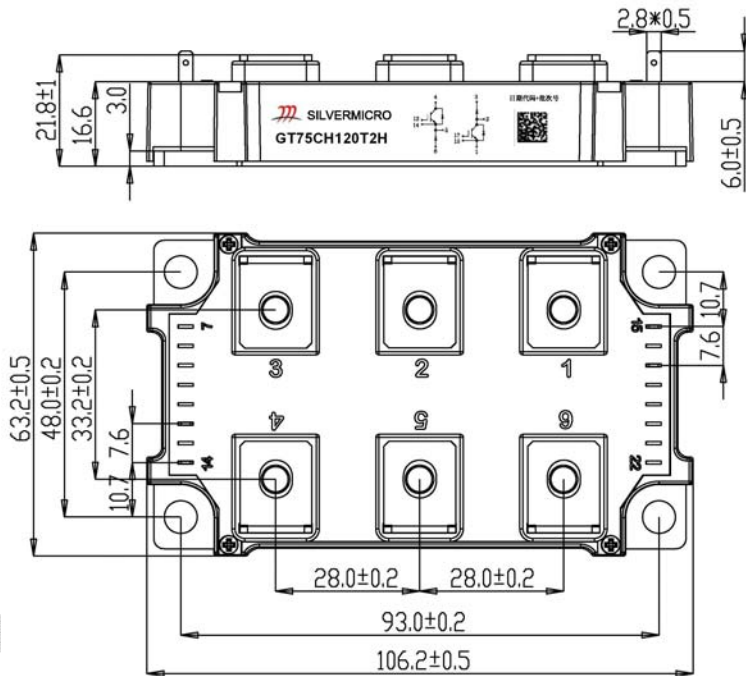


**Fig.11 Reverse Bias Safe Operation Area (RBSOA)**

**Internal Circuit:**



**Package Outline (Unit: mm):**



**Announcement**

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